EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	13	(((quantum near2 well) or QW) with (strain$3 or stain$3)) and ((light ADJ3 emit$4 ADJ3 device) or (light-emit$4 ADJ3 device) or LED) and active and clad$4 and substrate and (barrier near3 (InGaP or InGaAsP or GaAsP)) and (((guid$4 or waveguide) near2 (layer or medium or region or film)) with ((aluminum near3 galium near3 arsenide) or (Al?Ga????As or AsGa????Al? or Al?AsGa???? or Ga????Al?As or Ga????AsAl? or AsAl?Ga???? or AlGaAs or AlAsGa or GaAlAs or GaAsAl or AsAlGa or AsGaAl)))	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/08/18 08:23
L2	34	(((quantum near2 well) or QW) with (strain$3 or stain$3)) and ((light ADJ3 emit$4 ADJ3 device) or (light-emit$4 ADJ3 device) or LED or laser) and active and clad$4 and substrate and (barrier near3 (InGaP or InGaAsP or GaAsP)) and (((guid$4 or waveguide) near2 (layer or medium or region or film)) with ((aluminum near3 galium near3 arsenide) or (Al?Ga????As or AsGa????Al? or Al?AsGa???? or Ga????Al?As or Ga????AsAl? or AsAl?Ga???? or AlGaAs or AlAsGa or GaAlAs or GaAsAl or AsAlGa or AsGaAl)))	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/08/18 08:26
L4	21	(((quantum near2 well) or QW) with (strain$3 or stain$3)) and ((light ADJ3 emit$4 ADJ3 device) or (light-emit$4 ADJ3 device) or LED or laser) and active and clad$4 and substrate and (barrier near3 (InGaP or InGaAsP or GaAsP)) and ((guid$4 or waveguide) near3 ((aluminum near3 galium near3 arsenide) or (Al?Ga????As or AsGa????Al? or Al?AsGa???? or Ga????Al?As or Ga????AsAl? or AsAl?Ga???? or AlGaAs or AlAsGa or GaAlAs or GaAsAl or AsAlGa or AsGaAl)))	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/08/18 08:29
L3	21	(((quantum near2 well) or QW) with (strain$3 or stain$3)) and ((light ADJ3 emit$4 ADJ3 device) or (light-emit$4 ADJ3 device) or LED or laser) and active and clad$4 and substrate and (barrier near3 (InGaP or InGaAsP or GaAsP)) and (((guid$4 or waveguide) near2 (layer or medium or region or film)) near3 ((aluminum near3 galium near3 arsenide) or (Al?Ga????As or AsGa????Al? or Al?AsGa???? or Ga????Al?As or Ga????AsAl? or AsAl?Ga???? or AlGaAs or AlAsGa or GaAlAs or GaAsAl or AsAlGa or AsGaAl)))	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/08/18 08:29
L5	46	(((quantum near2 well) or QW) with (strain$3 or stain$3)) and ((light ADJ3 emit$4 ADJ3 device) or (light-emit$4 ADJ3 device) or LED or laser) and active and clad$4 and substrate and (barrier near3 (InGaP or InGaAsP or GaAsP)) and ((guid$4 or waveguide) with ((aluminum near3 galium near3 arsenide) or (Al?Ga????As or AsGa????Al? or Al?AsGa???? or Ga????Al?As or Ga????AsAl? or AsAl?Ga???? or AlGaAs or AlAsGa or GaAlAs or GaAsAl or AsAlGa or AsGaAl)))	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/08/18 08:51
L6	0	(((quantum near2 well) or QW) with (strain$3 or stain$3)) and ((light ADJ3 emit$4 ADJ3 device) or (light-emit$4 ADJ3 device) or LED or laser) and active and clad$4 and substrate and (barrier near3 (InGaP or InGaAsP or GaAsP)) and ((guid$4 or waveguide) with ((aluminum near3 galium near3 arsenide) or (Al?Ga????As or AsGa????Al? or Al?AsGa???? or Ga????Al?As or Ga????AsAl? or AsAl?Ga????)))	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/08/18 08:52
L9	4	("5744829" | "6181721" | "6449299").PN. OR ("6841409"). URPN.	US-PGPUB; USPAT; USOCR	AND	ON	2006/08/18 09:03
L8	1	("6841409").PN.	US-PGPUB; USPAT	OR	OFF	2006/08/18 09:03
L7	0	(((quantum near2 well) or QW) with (strain$3 or stain$3)) and ((light ADJ3 emit$4 ADJ3 device) or (light-emit$4 ADJ3 device) or LED or laser) and active and clad$4 and substrate and (barrier near3 (InGaP or InGaAsP or GaAsP)) and ((guid$4 or waveguide or (wave near1 guide)) with ((aluminum near3 galium near3 arsenide) or (Al?Ga????As or AsGa????Al? or Al?AsGa???? or Ga????Al?As or Ga????AsAl? or AsAl?Ga????)))	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/08/18 09:13

L11	0	(((quantum near2 well) or QW) with (strain$3 or stain$3)) and ((light ADJ3 emit$4 ADJ3 device) or (light-emit$4 ADJ3 device) or LED or laser) and active and clad$4 and substrate and (barrier near3 (InGaP or InGaAsP or GaAsP)) and ((aluminum near3 galium near3 arsenide) or (Al?Ga????As or AsGa????Al? or Al?AsGa???? or Ga????Al?As or Ga????AsAl? or AsAl?Ga????))	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/08/18 09:17
L10	0	(((quantum near2 well) or QW) with (strain$3 or stain$3)) and ((light ADJ3 emit$4 ADJ3 device) or (light-emit$4 ADJ3 device) or LED or laser) and active and clad$4 and substrate and (barrier near3 (InGaP or InGaAsP or GaAsP)) and ((guid$4 or waveguide or (wave near1 guide) or confinement) with ((aluminum near3 galium near3 arsenide) or (Al?Ga????As or AsGa????Al? or Al?AsGa???? or Ga????Al?As or Ga????AsAl? or AsAl?Ga????)))	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/08/18 09:29
L12	0	(((quantum near2 well) or QW) with (strain$3 or stain$3)) and ((light ADJ3 emit$4 ADJ3 device) or (light-emit$4 ADJ3 device) or LED or laser) and active and clad$4 and (substrate near3 (GaAs or AsGa)) and (barrier near3 (InGaP or InPGa or PGaIn or PInGa or InGaAsP or InGaPAs or InPGaAs or InASPGa or GaPAs or GaAsP)) and ((guid$4 or waveguide or (wave near1 guide) or confinement) and ((aluminum near3 galium near3 arsenide) or (Al?Ga????As or AsGa????Al? or Al?AsGa???? or Ga????Al?As or Ga????AsAl? or AsAl?Ga????)))	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/08/18 09:32
L13	102	(((quantum near2 well) or QW) with (strain$3 or stain$3)) and ((light ADJ3 emit$4 ADJ3 device) or (light-emit$4 ADJ3 device) or LED or laser) and active and clad$4 and (substrate near3 (GaAs or AsGa)) and (barrier near3 (InGaP or InPGa or PGaIn or PInGa or InGaAsP or InGaPAs or InPGaAs or InASPGa or GaPAs or GaAsP)) and ((guid$4 or waveguide or (wave near1 guide) or confinement) and ((aluminum near3 galium near3 arsenide) or (Al?Ga????As or AsGa????Al? or Al?AsGa???? or Ga????Al?As or Ga????AsAl? or AsAl?Ga???? or AlGaAs or AlAsGa or GaAlAs or GaAsAl or AsAlGa or AsGaAl)))	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/08/18 10:03